

AS4C1G16D4-62BIN vs AS4C1G16D4A-62BCN Comparison

| Part Number & result Parameter | AS4C1G16D4-62BIN | AS4C1G16D4A-62BCN | Comparison Result |
|--------------------------------------------|------------------------------------------------------|------------------------------------------------------|-------------------|
| Product Description | DDR4 SDRAM | DDR4 SDRAM | Same |
| Capacity | 16Gb (1G x 16) | 16Gb (1G x 16) | Same |
| Memory Organization | 128Meg, x16bits, x8 banks | 128Meg, x16bits, x8 banks | Same |
| Operating Power Supply | V _{DD} & V _{DDQ} = 1.2V (+/- 60mV) | V _{DD} & V _{DDQ} = 1.2V (+/- 60mV) | Same |
| | V _{pp} = 2.5V (-125mV,+250mV) | V _{pp} = 2.5V (-125mV,+250mV) | Same |
| Operating Temperature | Industrial (-40°C≤Tc≤+95°C) | Commercial (0°C ≤ Tc ≤ +95°C) | Different |
| Max Clock Frequency | 1600 MHz | 1600 MHz | Same |
| Min. Cycle Time | 0.625ns | 0.625ns | Same |
| Max Data Rate | 3200 Mbps | 3200 Mbps | Same |
| CAS Latency | 22 | 22 | Same |
| tAA(ns) | 13.75 | 13.75 | Same |
| tRCD (ns) | 13.75 | 13.75 | Same |
| tRP (ns) | 13.75 | 13.75 | Same |
| Number of Bank groups | 2 | 2 | Same |
| Bank Count per Group | 4 | 4 | Same |
| Row Addressing | 128K (A0..A16) | 128K (A0..A16) | Same |
| Column Addressing | 1K (A0..9) | 1K (A0..9) | Same |
| Page Size per bank | 2KB | 2KB | Same |
| Temperature controlled Refresh time | 64ms at 0C ~ 85C 32ms at 85C ~ 95C | 64ms at 0C ~ 85C 32ms at 85C ~ 95C | Same |
| Low Power Auto Self Refresh support | Yes | Yes | Same |
| I/O Capacitance | CIO = 0.82pF Max | CIO = 0.82pF Max | Same |
| Pin to Pin Compatible | Pin to Pin Compatible | | |
| AC/DC Characteristics | Same | | Meet JEDEC |



12815 NE 124th St STE#D, Kirkland, WA-98034

| AS4C1G16D4-62BIN vs AS4C1G16D4A-62BCN Comparison | | | |
|---------------------------------------------------------|----------------------------------------------------------------|-----------------------------------------------------------------|------------------------------|
| | AS4C1G16D4-62BIN | AS4C1G16D4A-62BCN | Comparison Result |
| IDD Spec conditions | -40C ≤ Tc ≤ 95C | 0C ≤ Tc ≤ 95C | |
| I_{DD0} (mA) , I_{pp0} (mA) | 70, 4 | 70, 4 | Same |
| I_{DD1} (mA) | 90 | 84 | Rev.A better |
| I_{DD2N} (mA) | 50 | 45 | Comparable |
| I_{DD2NT} (mA) | 58 | 58 | Same |
| I_{DD2P} (mA) | 43 | 38 | Comparable |
| I_{DD2Q} (mA) | 47 | 42 | Comparable |
| I_{DD3N} (mA) | 62 | 62 | Same |
| I_{DD3P} (mA) | 51 | 51 | Same |
| I_{DD4R} (mA) | 299 | 193 | Rev.A better |
| I_{DD4W/A/B} (mA) | 236 | 141 | Rev.A better |
| I_{DD6N} (mA) | 57 | 53 | Comparable |
| I_{DD6R} (mA) | 24 | 20 | Comparable |
| I_{DD6E} (mA) | 113 | 90 | Rev.A better |
| I_{DD7} (mA) | 251 | 200 | Rev.A better |
| Package | 96b FBGA 9x13x1.2mm | 96b FBGA 7.5x13x1.2mm | Rev.A smaller, comparable |
| Solder Ball material Composition | SACQ (92.45% Sn, 4% Ag, 0.5% Cu, 3% Bi, 0.05% Ni) | SACQ (92.45% Sn, 4% Ag, 0.5% Cu, 3% Bi, 0.05% Ni). | Same |
| Package Material | Pb and Halogen Free | Pb and Halogen Free | Same |